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BLF3G21-6

UHF power LDMOS transistor

Rev. 3 — 1 September 2015

AMPLEON

Product data sheet

1. Product profile

1.1 General description

 $6~\mathrm{W}$ LDMOS power transistor for base station applications at frequencies from HF to 2200 MHz

Table 1. Typical class-AB RF performance

 I_{Dq} = 90 mA; T_h = 25 °C in a common source test circuit.

Mode of operation	f	PL	Gp	η _D	IMD3	P _{L(1dB)}
	(MHz)	(W)	(dB)	(%)	(dB)	(W)
CW	2000	7	12.5	43	-	7
Two-tone	2000	6	15.5	39	-32	-
		< 2	15.8	-	< -50	-

Table 2. Typical class-A RF performance

 I_{Dq} = 200 mA; T_h = 25 °C in a modified PHS test fixture.

Mode of operation	f	P _{L(AV)}	Gp	η_D	ACPR _{600k}
	(MHz)	(W)	(dB)	(%)	(dBc)
PHS	1880 to 1920	2	16	20	-75

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Excellent back-off linearity
- Typical PHS performance at a supply voltage of 26 V and I_{Dq} of 200 mA:
 - ◆ Average output power = 2 W
 - ◆ Power gain = 16 dB
 - ◆ Efficiency = 20 %
 - ◆ ACPR_{600k} = -75 dBc
- Easy power control
- Excellent ruggedness
- High power gain
- Excellent thermal stability
- Designed for broadband operation (HF to 2200 MHz)

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- No internal matching for broadband operation
- ESD protection

1.3 Applications

- RF power amplifiers for GSM, PHS, EDGE, CDMA and W-CDMA base stations and multicarrier applications in the HF to 2200 MHz frequency range
- Broadcast drivers

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain	a .	
2	gate		.∟¹
3	source		2 — 3 sym112

^[1] Connected to flange.

3. Ordering information

Table 4. Ordering information

Type number	Package	Package			
	Name	Description	Version		
BLF3G21-6	-	ceramic surface-mounted package; 2 leads	SOT538A		

4. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	±13	V
I_D	drain current		-	2.3	Α
T_{stg}	storage temperature		-65	+200	°C
T _j	junction temperature		-	200	°C

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5. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_h = 25 ^{\circ}C; P_{L(AV)} = 15 W$	<u>11</u> 10	K/W

^[1] Thermal resistance is determined under specified RF operating conditions.

6. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.13 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 13 mA	2.0	2.6	3.0	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 6 V;$ $V_{DS} = 10 V$	1.85	2.3	-	Α
I_{GSS}	gate leakage current	V_{GS} = ±15 V; V_{DS} = 0 V	-	-	140	nA
g _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 0.5 A	-	0.6	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 9 \text{ V}; I_D = 0.5 \text{ A}$	-	1.6	2.07	Ω
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V};$ f = 1 MHz	-	0.3	-	pF

7. Application information

Table 8. Application information

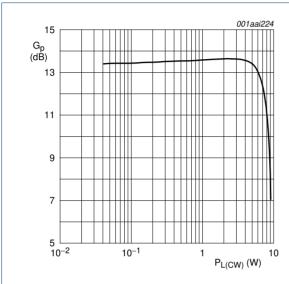
 V_{DS} = 26 V; T_h = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Mode of ope	eration: Two-tone CW (100 k	Hz tone spacing); f = 20	000 MHz	z; I _{Dq} = 9	0 mA		
G _p	power gain	$P_{L(PEP)} = 6 W$	14	15.5	-	dB	
RLin	input return loss	$P_{L(PEP)} = 6 W$	-	-7	-3	dB	
η_{D}	drain efficiency	$P_{L(PEP)} = 6 W$	35	39	-	%	
IMD3 third order intermodulation distortion	$P_{L(PEP)} = 6 W$	-	-32	-29	dBc		
	distortion	P _{L(PEP)} < 2 W	-	< -50	-	dBc	
Mode of ope	Mode of operation: one-tone CW; f = 2000 MHz; I _{Dq} = 90 mA						
Gp	power gain	$P_L = P_{L(1dB)} = 7 \text{ W}$	-	12.5	-	dB	
η_{D}	drain efficiency	$P_L = P_{L(1dB)} = 7 \text{ W}$	-	43	-	%	
Mode of ope	eration: PHS; f = 1900 MHz;	I _{Dq} = 200 mA					
G _p	power gain	P _{L(AV)} = 2 W	-	16	-	dB	
η_{D}	drain efficiency	P _{L(AV)} = 2 W	-	20	-	%	
ACPR _{600k}	adjacent channel power ratio (600 kHz)	$P_{L(AV)} = 2 W$	-	-75	-	dBc	

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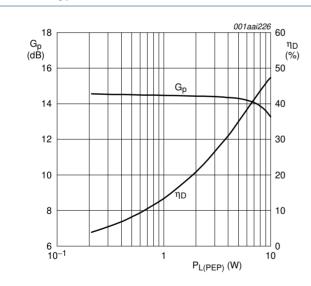
7.1 Ruggedness in class-AB operation

The BLF3G21-6 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 26 V; f = 2200 MHz at rated load power.



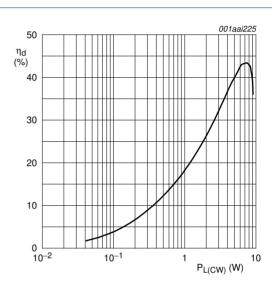
 V_{DS} = 26 V; I_{Dq} = 90 mA; T_h = 25 °C; f = 2000 MHz.

Fig 1. Power gain as a function of CW load power; typical values



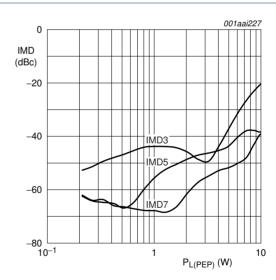
 V_{DS} = 26 V; I_{Dq} = 90 mA; $T_h \leq$ 25 °C; f_1 = 2000 MHz; f_2 = 2000.1 MHz.

Fig 3. Two-tone power gain and drain efficiency as function of peak envelope load power; typical values



 V_{DS} = 26 V; I_{Dq} = 90 mA; T_h = 25 °C; f = 2000 MHz.

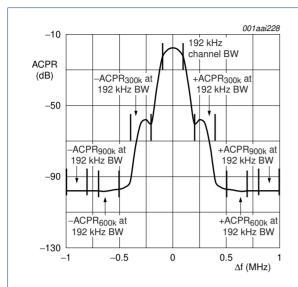
Fig 2. Drain efficiency as a function of CW load power; typical values



 V_{DS} = 26 V; I_{Dq} = 90 mA; $T_h \le$ 25 °C; f_1 = 2000 MHz; f_2 = 2000.1 MHz.

Fig 4. Two-tone intermodulation distortion as a function of peak envelope load power; typical values

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 V_{DS} = 26 V; I_{Dq} = 200 mA; $T_h \le$ 25 °C; f_c = 1900 MHz; $P_{L(AV)}$ = 2 W.

Fig 5. ACPR performance under PHS conditions, measured in application board.

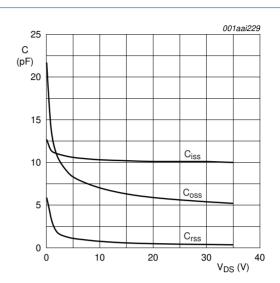
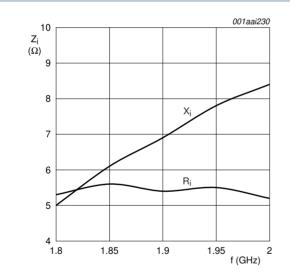
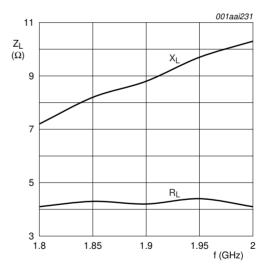


Fig 6. C_{iss}, C_{rss} and C_{oss} as function of drain supply voltage; typical values.



 V_{DS} = 26 V; I_{Dq} = 90 mA; P_L = 45 W; $T_h \leq$ 25 °C.

Fig 7. Input impedance as a function of frequency (series components); typical values

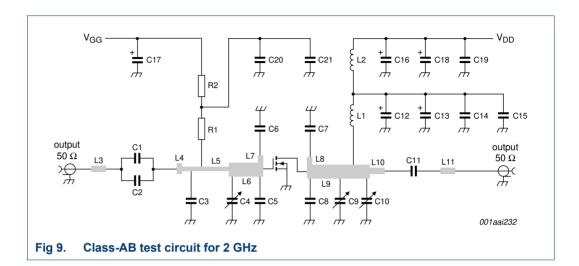


 V_{DS} = 26 V; I_{Dq} = 90 mA; P_{L} = 45 W; $T_{h} \le$ 25 °C.

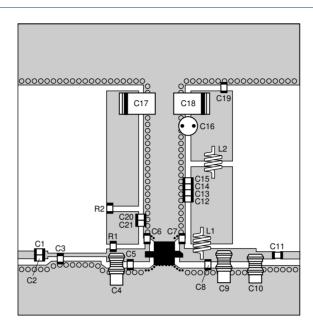
Fig 8. Load impedance as a function of frequency (series components); typical values

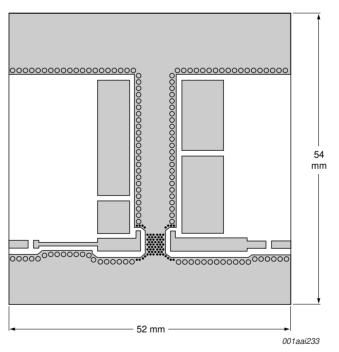
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Test information 8.



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Dimensions in mm.

The components are situated on one side of the copper-clad Printed-Circuit Board (PCB) with Teflon dielectric (ϵ_r = 2.2); thickness = 0.51 mm.

The other side is unetched and serves as a ground plane.

See Table 9 for list of components.

Fig 10. Component layout for 2 GHz class-AB test circuit

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Table 9. List of components (see Figure 9 and Figure 10)

Component	Description		Value	Remarks
C1, C2, C11	multilayer ceramic chip capacitor	<u>[1]</u>	6.8 pF	
C4, C10	Tekelec variable capacitor; type 37281		0.4 pF to 2.5 pF	
C6	multilayer ceramic chip capacitor	[1]	2.7 pF	
C7	multilayer ceramic chip capacitor	[1]	2.0 pF	
C8	multilayer ceramic chip capacitor	[1]	0.2 nF	
C9	Tekelec variable capacitor; type 37281		0.6 pF to 4.5 pF	
C12	multilayer ceramic chip capacitor	[1]	10 pF	
C13	multilayer ceramic chip capacitor	[1]	51 pF	
C14	multilayer ceramic chip capacitor	[1]	120 pF	
C15	multilayer ceramic chip capacitor		100 nF	
C16	electrolytic capacitor		100 μF; 63 V	
C17, C18	tantalum SMD capacitor		10 μF; 35 V	
C19	multilayer ceramic chip capacitor	[2]	1 nF	
C20	multilayer ceramic chip capacitor	[1]	22 pF	
C21	multilayer ceramic chip capacitor	[1]	560 pF	
L1, L2	3 turns enamelled copper wire	[3]	D = 2 mm; d = 0.8 mm; length = 3 mm	
L3	stripline	[3]	50 Ω	(L \times W) 3.5 mm \times 1.5 mm
L3	stripline	[3]	34.3 Ω	(L \times W) 1.0 mm \times 1.5 mm
L4	stripline	[3]	50 Ω	(L \times W) 11.0 mm \times 0.8 mm
L5	stripline	[3]	34.3 Ω	(L \times W) 8.0 mm \times 3.0 mm
L6	stripline	[3]	23.6 Ω	(L \times W) 1.5 mm \times 1.0 mm
L7, L8	stripline	[3]	5.6 Ω	(L \times W) 14.4 mm \times 3.0 mm
L9	stripline	[3]	3.5 Ω	(L \times W) 3.5 mm \times 1.5 mm
L10, L11	stripline	[3]	31.9 Ω	(L \times W) 12.0 mm \times 1.9 mm
R1	SMD resistor		470 Ω	
R2	SMD resistor		1 kΩ	

^[1] American Technical Ceramics type 100A or capacitor of same quality.

^[2] American Technical Ceramics type 100B or capacitor of same quality.

^[3] The striplines are on a double copper-clad Printed-Circuit Board (PCB) with Rogers 5880 dielectric (ϵ_r = 2.2); thickness = 0.51 mm.

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9. Package outline

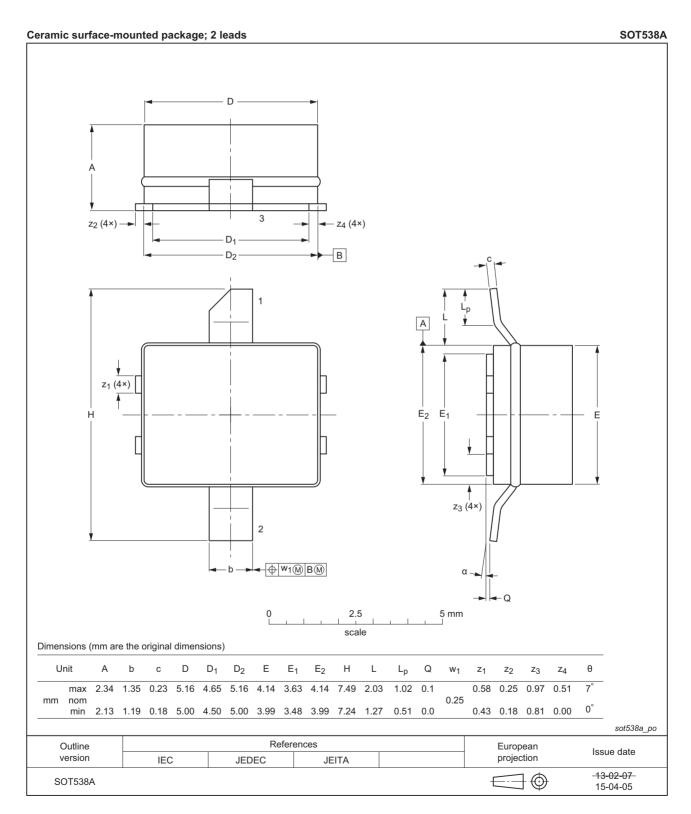


Fig 11. Package outline SOT538A

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10. Abbreviations

Table 10. Abbreviations

Acronym	Description	
CDMA	Code Division Multiple Access	
EDGE	Enhanced Data rates for GSM Evolution	
GSM	Global System for Mobile communications	
HF	High Frequency	
LDMOS	Laterally Diffused Metal-Oxide Semiconductor	
PHS	Personal Handy-phone System	
RF	Radio Frequency	
SMD	Surface Mount Device	
UHF	Ultra High Frequency	
VSWR	Voltage Standing-Wave Ratio	
W-CDMA	Wideband Code Division Multiple Access	

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF3G21-6#3	20150901	Product data sheet	-	BLF3G21-6 v.2	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 				
BLF3G21-6 v.2	20130411	Product data sheet	-	BLF3G21-6 v.1	
BLF3G21-6 v.1	20080625	Product data sheet	-	-	

BLF3G21-6 AMAPLEON

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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